



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re application of:

Calvez et al.

Group Art Unit: Unknown

Serial No. 10/550,843

Examiner: N/A

Filed: March 24, 2004 (I.A.)

For: IMPROVEMENTS IN AND
RELATING TO VERTICAL-
CAVITY SEMICONDUCTOR
OPTICAL DEVICES

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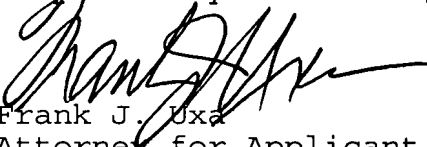
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INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to call to the attention of the Examiner the documents cited on the accompanying Form PTO-1449. No concession is made that these documents are prior art, and applicant expressly reserves the right to antedate the documents as may be appropriate. Applicant requests that each of these documents be made of record in the above-identified application.

Respectfully submitted,


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Form PTO-1449

APR 20 2007

Docket No.: D-3214

Application No.: 10/550,843

**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**
(Use several sheets if necessary)

Applicant: Calvez et al.

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U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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						YES	NO
	WO 95/25366	09/1995	International				
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AA	W.J. Alford et al., "High Power and good beam quality at 980 nm from a vertical external-cavity surface-emitting laser", <i>Journal of the Optical Society of America B (Optical Physics) Opt. Soc. America USA</i> , Vol. 19, No. 4, pages 663-666, 2002.
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AD	W.W. Bewley et al, "Thermal Characterization of Diamond-Pressure-Bond Heat Sinking for Optically Pumped Mid-Infrared Lasers", <i>IEEE Journal of Quantum Electronics</i> , Vol. 35, No. 11, 1999, p. 1597-1601.
AE	E. Staffan Björin, "High Gain, High Efficiency Vertical-Cavity Semiconductor Optical Amplifiers", <i>IPRM</i> , 2002, p. 307-310.
AF	A. Black, "Wafer Fusion: Materials Issues and Device Results", <i>IEEE Journal Sel. Topics in Quantum Electronics</i> , Vol. 3, No. 3, 1997, p. 943-951.

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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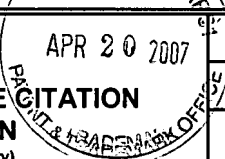
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BU	F. Yang et al., "Edge-emitting quantum well laser with Bragg reflectors", <i>Appl. Phys. Lett.</i> , Vol. 66, No. 22, 1995 , p. 2949-2951.
BV	Coherent Laser Division. Sapphire Optically Pumped Semiconductor Lasers, Copyright 2002, Coherent, Inc.
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